



Attorney Docket No. ASC-023DVC2
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Eugene A. Fitzgerald

Application No. 10/022,689

Filed: December 17, 2001

Art Unit: 2813

Title: CONTROLLING THREADING
DISLOCATION DENSITIES IN GE ON SI
USING GRADED GESI LAYERS AND
PLANARIZATION

Examiner: Laura Schillinger

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

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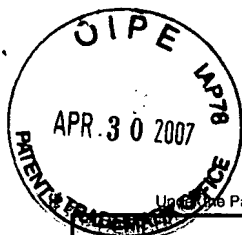
It is respectfully requested that the references listed on the attached Form PTO/SB/08, and other information contained herein, be made of record in this application.

Dated: *Apr 12, 2007*

Respectfully submitted,

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PTO/SB/08A/B (09-06)

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet	1	of	3	Attorney Docket Number	ASC-023DVC2
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Complete if Known

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First Named Inventor	Eugene A. Fitzgerald
Art Unit	2813
Examiner Name	Laura Schillinger
Attorney Docket Number	ASC-023DVC2

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	A1	US-4,704,302	11-03-1987	Bruel et al.	
	A2	US-5,405,802	04-11-1995	Yamagata et al.	
	A3	US-5,426,316	06-20-1995	Mohammad	
	A4	US-5,705,421	01-06-1998	Matsushita et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	C1	Batterman, "Hillocks, Pits, and Etch Rate in Germanium Crystals," 28 J. Appl. Physics 11, pp. 1236-1241 (1957).	
	C2	Bohg, "Ethylene Diamine-Pyrocatechol-Water Mixture Shows Etching Anomaly in Boron-Doped Silicon," 118 J. Electrochemical Soc'y 2, pp. 401-402 (1971).	
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	C8	Fitzgerald, "GeSi/Si Nanostructures," Annual Rev. of Mat. Sci., Vol. 25, pp. 417-454 (1995).	
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	C10	Ghandi et al., "Chemical Etching of Germanium," 135 J. Electrochemical Soc'y 8, pp. 2053-2054 (1988).	
	C11	Godbey et al., "A Si _{0.7} Ge _{0.3} strained-layer etch stop for the generation of thin layer undoped silicon," 56 Applied Physics Letters 4, pp. 373-375 (1990).	
	C12	Herzog et al., "X-Ray Investigation of Boron- and Germanium-Doped Silicon Epitaxial Layers," 131 J. Electrochemical Soc'y 12, pp. 2969-2974 (1984).	

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				Art Unit	2813
				Examiner Name	Laura Schillinger
Sheet	2	of	3	Attorney Docket Number	ASC-023DVC2

C13	Holmes, "The Orientation Dependence of Etching Effects on Germanium Crystals," 7 Acta Metallurgica 4, pp. 283-290 (1959).	
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C28	Palik et al., "Ellipsometric Study of the Etch-Stop Mechanism in Heavily Doped Silicon," 132 J. Electrochemical Society 1, pp. 135-141 (1985).	
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C35	Ransom et al., "Gate-Self-Aligned n-channel and p-channel Germanium MOSFET's," 38 IEEE Trans. on Electron Devices 12, pp. 2695 (1991).	

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	C36	Seidel et al., "Anisotropic Etching of Crystalline Silicon in Alkaline Solutions," 137 J. Electrochemical Soc'y 11, pp. 3626-3632 (1990).	
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	C43	Vol'fson et al., "Fundamental Absorption Edge of Silicon Heavily Doped with Donor or Acceptor Impurities," 1 Soviet Physics Semiconductors 3, pp. 327-332 (1967).	
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